October 2001

FAIRCHILD

FDN327N

N-Channel 1.8 Vgs Specified PowerTrench[®] MOSFET

General Description

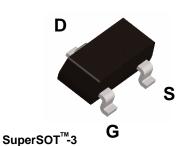
This 20V N-Channel MOSFET uses Fairchild's high voltage PowerTrench process. It has been optimized for power management applications.

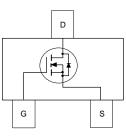
Applications

- Load switch
- Battery protection
- Power management

Features

- Low gate charge (4.5 nC typical)
- Fast switching speed
- + High performance trench technology for extremely low $R_{\text{DS}(\text{ON})}$





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter			Ratings	Units	
V _{DSS}	Drain-Sourc	e Voltage		20		
V _{GSS}	Gate-Source Voltage			± 8		
ID	Drain Curre	nt – Continuous	(Note 1a)	2	А	
	– Pulsed			8		
PD	Power Dissipation for Single Operation		(Note 1a)	0.5	W	
			(Note 1b)	0.46		
T _J , T _{STG}	Operating and Storage Junction Temperature Range			–55 to +150 °C		
	I Charact		I			
	Thermal Resistance, Junction-to-Ambient (Note 1a)			250		
R _{θJA}	Thermal Re	sistance, Junction-to-Ambie	nt (Note 1a)	250	°C/W	
		sistance, Junction-to-Ambier sistance, Junction-to-Case	nt (Note 1a) (Note 1)	250 75		
R _{eJA} R _{eJC} Packag	Thermal Re	,	(Note 1)		°C/W °C/W	
_{R₀ıc} Packag	Thermal Re	sistance, Junction-to-Case g and Ordering In	(Note 1)			

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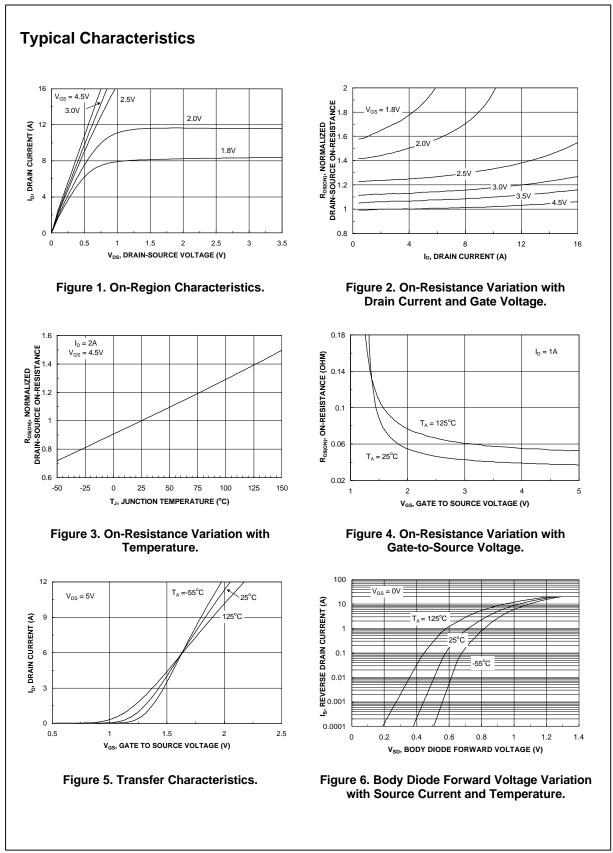
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					l
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 V$, $I_D = 250 \mu A$	20			V
<u>ΔBVdss</u> ΔTj	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		12		mV/°C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 16 V$, $V_{GS} = 0 V$			1	μΑ
GSSF	Gate-Body Leakage, Forward	$V_{GS} = 8 V$, $V_{DS} = 0 V$			100	nA
GSSR	Gate-Body Leakage, Reverse	$V_{GS} = -8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)	·	•		•	
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.4	0.7	1.5	V
$\Delta V_{GS(th)}$ ΔT_J	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		-3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$ \begin{array}{l} V_{GS} = 4.5 \ V, I_D = 2.0 \ A \\ V_{GS} = 2.5 \ V, I_D = 1.9 \ A \\ V_{GS} = 1.8 \ V, I_D = 1.6 \ A \\ V_{GS} = 4.5 \ V, \ I_D = 2 \ A, \ T_J = 125^\circ C \end{array} $		40 49 65 55	70 80 120 103	mΩ
D(on)	On–State Drain Current	$V_{GS} = 4.5V, V_{DS} = 5V$	8			Α
g _{FS}	Forward Transconductance	$V_{DS} = 5V,$ $I_D = 2A$		11		S
	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 10 V$, $V_{GS} = 0 V$		423		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		87		pF
C _{rss}	Reverse Transfer Capacitance			48		pF
Switchin	g Characteristics (Note 2)					
d(on)	Turn–On Delay Time	$V_{DD} = 10 V, \qquad I_D = 1 A,$		6	12	ns
r	Turn–On Rise Time	$V_{GS} = 4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		6.5	13	ns
d(off)	Turn–Off Delay Time			14	29	ns
f	Turn–Off Fall Time	_		2	4	ns
Ĵ	Total Gate Charge	$V_{DS} = 10 V$, $I_{D} = 2 A$,		4.5	6.3	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 4.5 V$		0.89		nC
Q _{gd}	Gate-Drain Charge			0.95		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings				
s	Maximum Continuous Drain-Source				0.42	Α
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V$, $I_S = 0.42 A$ (Note 2)		0.6	1.2	V
	um of the junction-to-case and case-to-ambient the is. R _{6JC} is guaranteed by design while R _{6CA} is dete a) 250°C/W when mounted on a 0.02 in pad of 2 oz. copper.			l as the so	lder mounti	ng surface

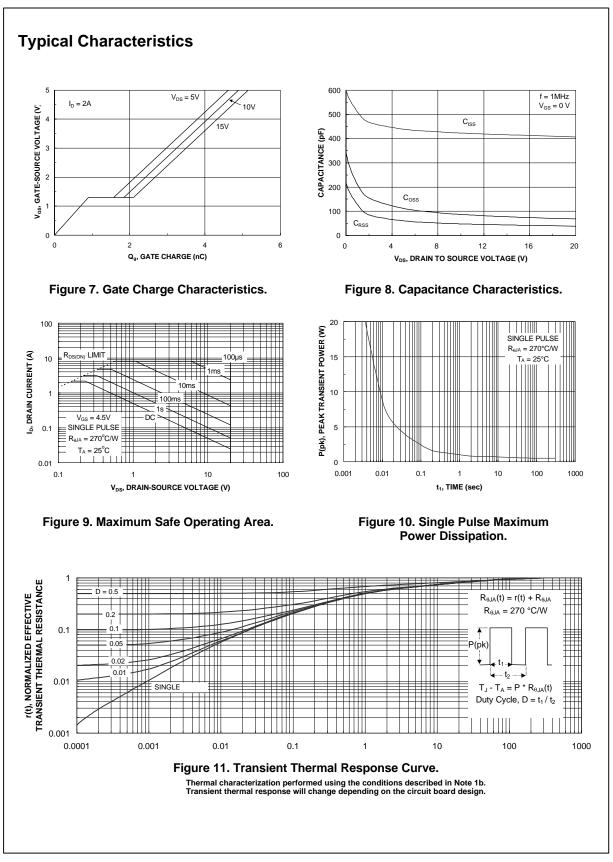
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

FDN327N Rev C (W)

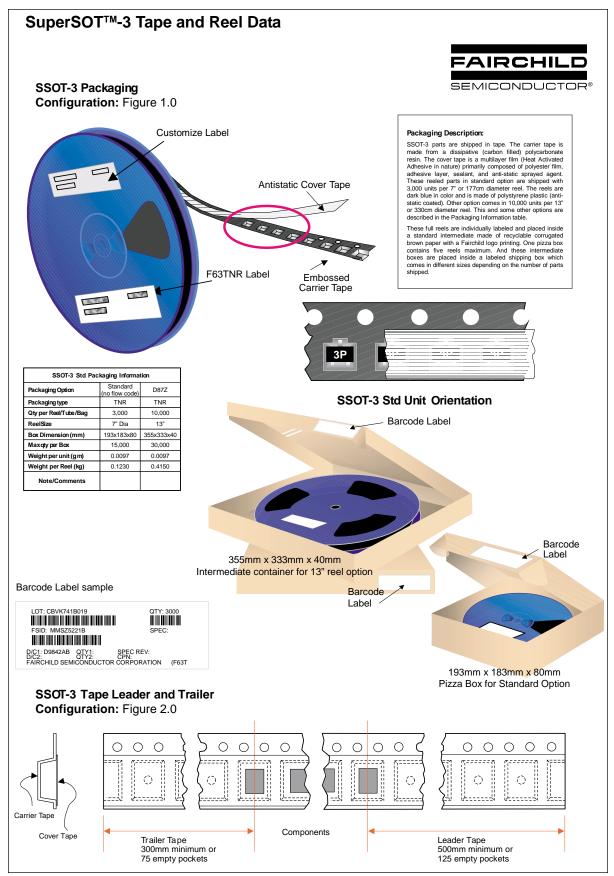


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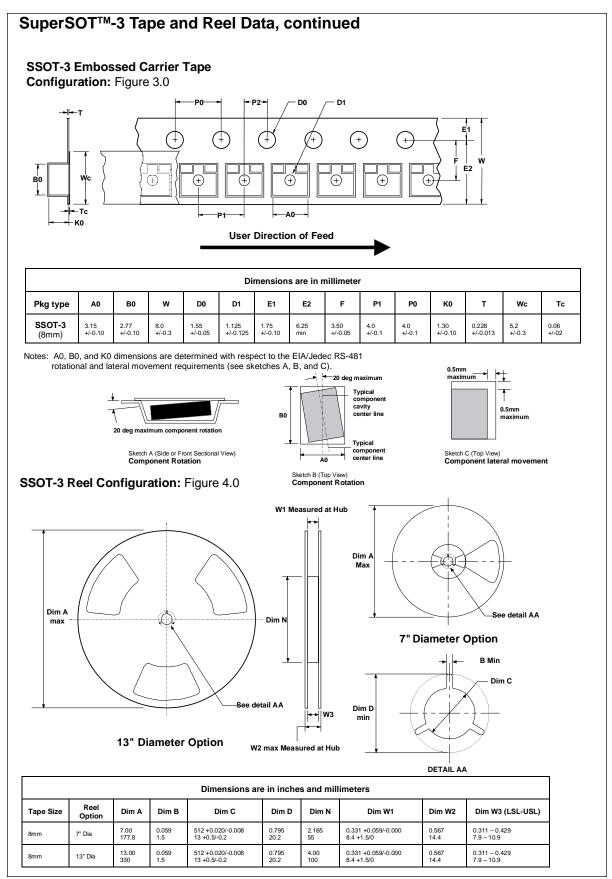
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FDN327N Rev C (W)

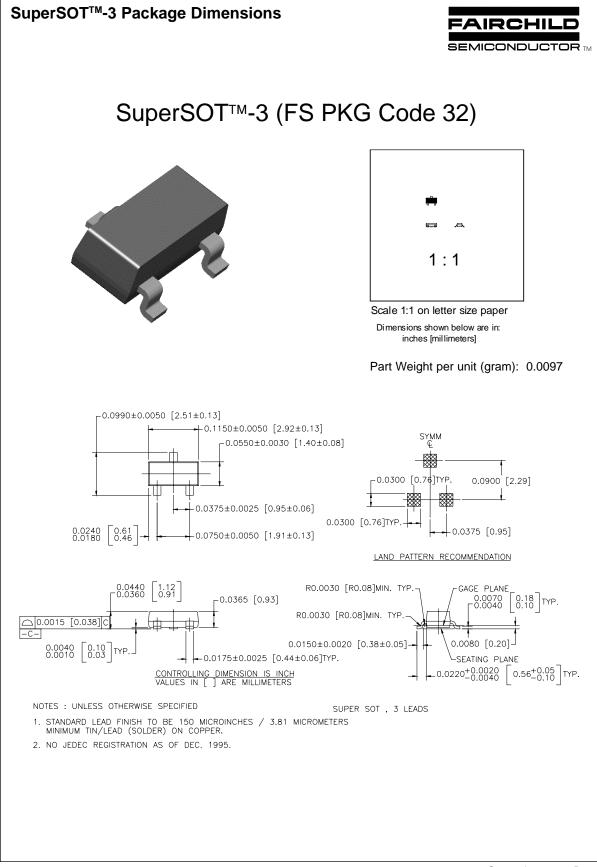


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July 1999, Rev. C



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